TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

2SC5086

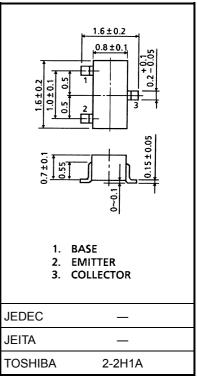
VHF~UHF Band Low Noise Amplifier Applications

Unit: mm

- Low noise figure, high gain.
- NF = 1.1dB, $|S_{21e}|^2 = 11dB$ (f = 1 GHz)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V_{CBO}	20	V	
Collector-emitter voltage	V _{CEO}	12	V	
Emitter-base voltage	V _{EBO}	3	V	
Base current	Ι _Β	40	mA	
Collector current	I _C	80	mA	
Collector power dissipation	P _C	100	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T _{stg}	-55~125	°C	



Weight: 2.4 mg (typ.)

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition		Тур.	Max	Unit	
Transition frequency	f _T	V _{CE} = 10 V, I _C = 20 mA	5	7	_	GHz	
Insertion gain	S _{21e} ² (1)	V _{CE} = 10 V, I _C = 20 mA, f = 500 MHz —		16.5	_	- dB	
	S _{21e} ² (2)	V _{CE} = 10 V, I _C = 20 mA, f = 1 GHz	11	_			
Noise figure	NF (1)	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}, f = 500 \text{ MHz}$	_	1	_	dB	
Noise ligure	NF (2)	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	_	1.1	2] ub	

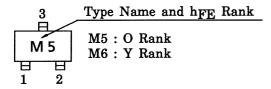
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 10 \text{ V}, I_{E} = 0$	_	_	1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 1 V, I _C = 0	_	_	1	μА
DC current gain	h _{FE} (Note 1)	V _{CE} = 10 V, I _C = 20 mA	80	_	240	
Output capacitance	C _{ob}	V _{CB} = 10 V, I _F = 0, f = 1 MHz (Note 2)	_	1.0	_	pF
Reverse transfer capacitance	C _{re}	$V_{CB} = 10 \text{ V}, I_{E} = 0, I = 1 \text{ IMIDZ} \text{ (NOTE 2)}$	_	0.65	1.15	pF

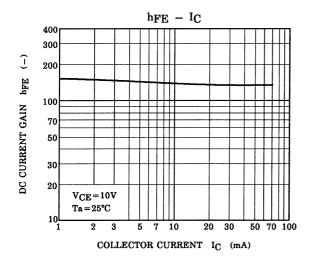
Note 1: hFE classification O: 80~160, Y: 120~240

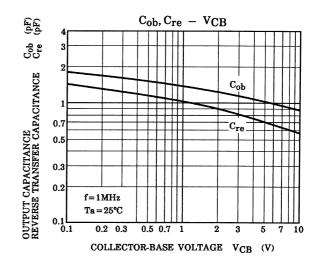
Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

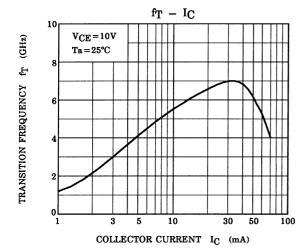
Marking

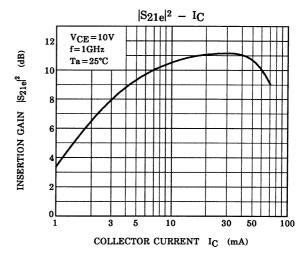


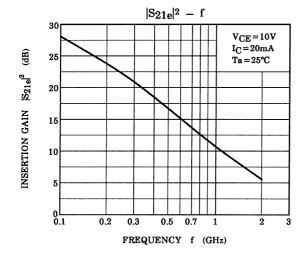
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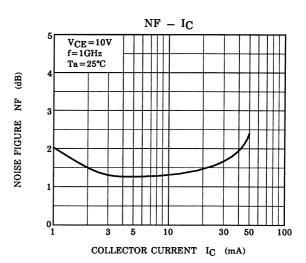




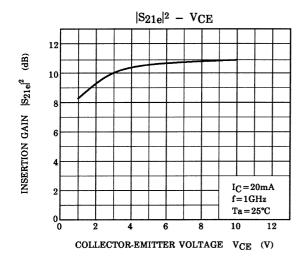


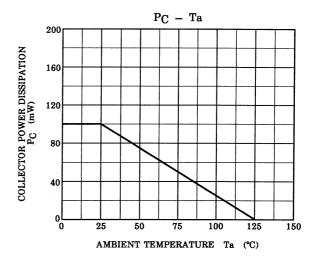






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S-Parameter $Z_O = 50 \Omega$, Ta = 25°C

$V_{\text{CE}} = 10 \ \text{V}, \ I_{\text{C}} = 5 \ \text{mA}$

Frequency	S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.715	-69.3	9.495	132.1	0.051	55.2	0.747	-29.0
400	0.542	-112.4	6.482	108.5	0.068	46.8	0.555	-35.1
600	0.476	-137.7	4.717	95.8	0.077	47.9	0.478	-36.2
800	0.447	-154.4	3.691	87.1	0.086	51.6	0.442	-37.1
1000	0.435	-166.8	3.049	79.9	0.096	55.9	0.424	-38.9
1200	0.433	-176.6	2.611	73.9	0.108	60.4	0.418	-41.8
1400	0.435	174.8	2.294	68.3	0.123	64.2	0.411	-45.0
1600	0.439	167.3	2.050	63.2	0.140	66.9	0.407	-49.0
1800	0.444	160.6	1.860	58.7	0.159	68.7	0.406	-53.6
2000	0.454	154.2	1.713	53.9	0.180	70.5	0.404	-57.8

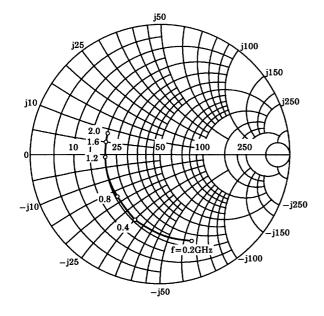
$V_{CE} = 10 \text{ V}, I_C = 20 \text{ mA}$

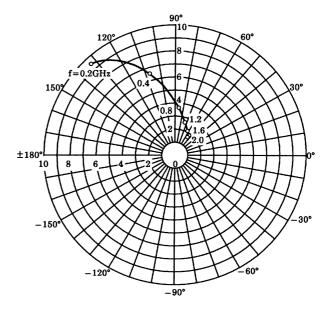
Frequency	S11		S21		S12		S22	
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.465	-107.8	16.512	113.2	0.035	56.7	0.484	-40.9
400	0.375	-145.6	9.090	96.5	0.052	62.2	0.331	-37.8
600	0.351	-164.4	6.252	88.1	0.070	66.5	0.291	-34.1
800	0.343	-176.7	4.762	81.9	0.089	68.9	0.277	-33.3
1000	0.338	174.8	3.875	76.6	0.109	70.2	0.273	-34.0
1200	0.337	167.9	3.285	71.8	0.130	70.8	0.274	-36.2
1400	0.343	161.6	2.874	67.2	0.152	70.6	0.274	-39.3
1600	0.343	156.2	2.553	62.9	0.173	69.8	0.274	-43.4
1800	0.348	151.2	2.317	58.8	0.195	68.9	0.273	-47.8
2000	0.354	146.2	2.113	55.0	0.218	68.2	0.272	-52.1

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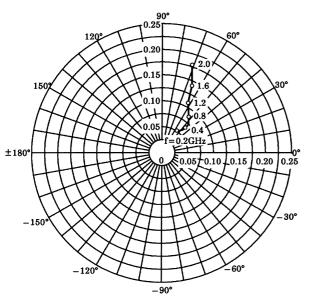
 $\begin{array}{l} S_{11e} \\ V_{CE} = 10V \\ I_{C} = 5mA \\ Ta = 25^{\circ}C \\ (UNIT:\Omega) \end{array}$

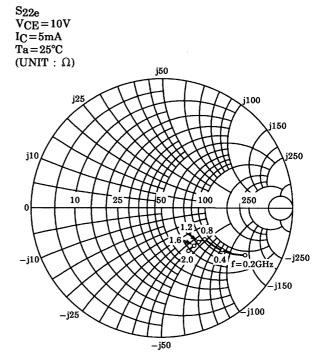






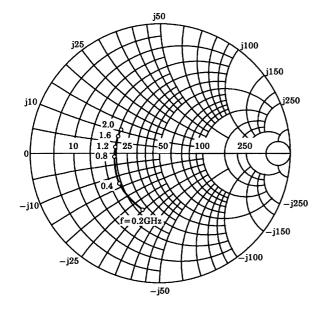
 $\begin{array}{l} S_{12e} \\ V_{CE} = 10V \\ I_{C} = 5 mA \\ Ta = 25 ^{\circ}C \end{array}$

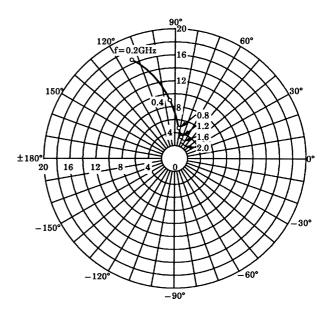




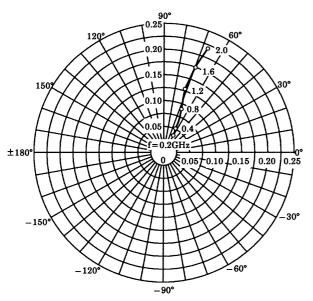
 $\begin{array}{l} S_{11e} \\ V_{CE} = 10V \\ I_{C} = 20 mA \\ Ta = 25 ^{\circ}C \\ (UNIT: \Omega) \end{array}$

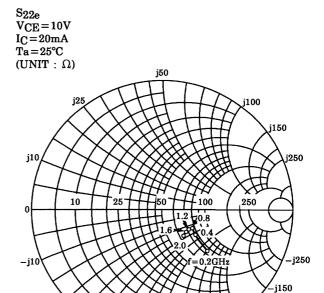






 $\begin{array}{l} S_{12e} \\ V_{CE} = 10V \\ I_{C} = 20 mA \\ Ta = 25 ^{\circ}C \end{array}$





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-j100

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